

# Wigner Solid Transport through a Point Constriction

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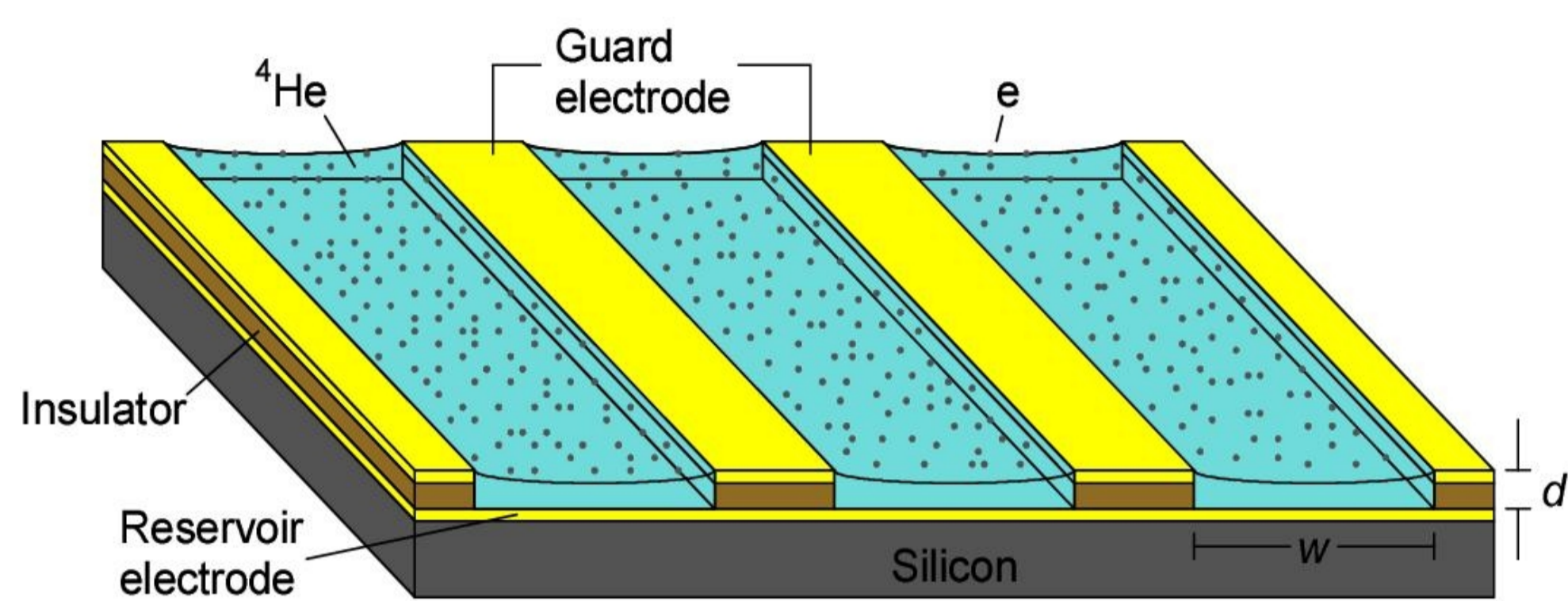
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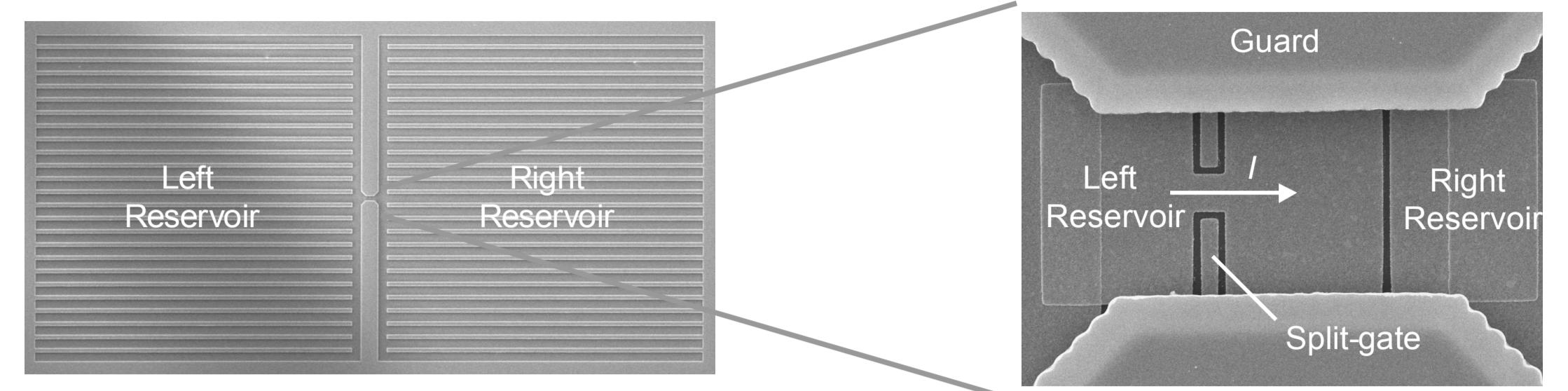
## Introduction – Microchannel Split-gate Device

Microchannels allow the manipulation of small numbers of surface electrons:  $n_s \sim 1 \times 10^9 \text{ cm}^{-2}$

Bulk properties (high mobility, Wigner solid) maintained



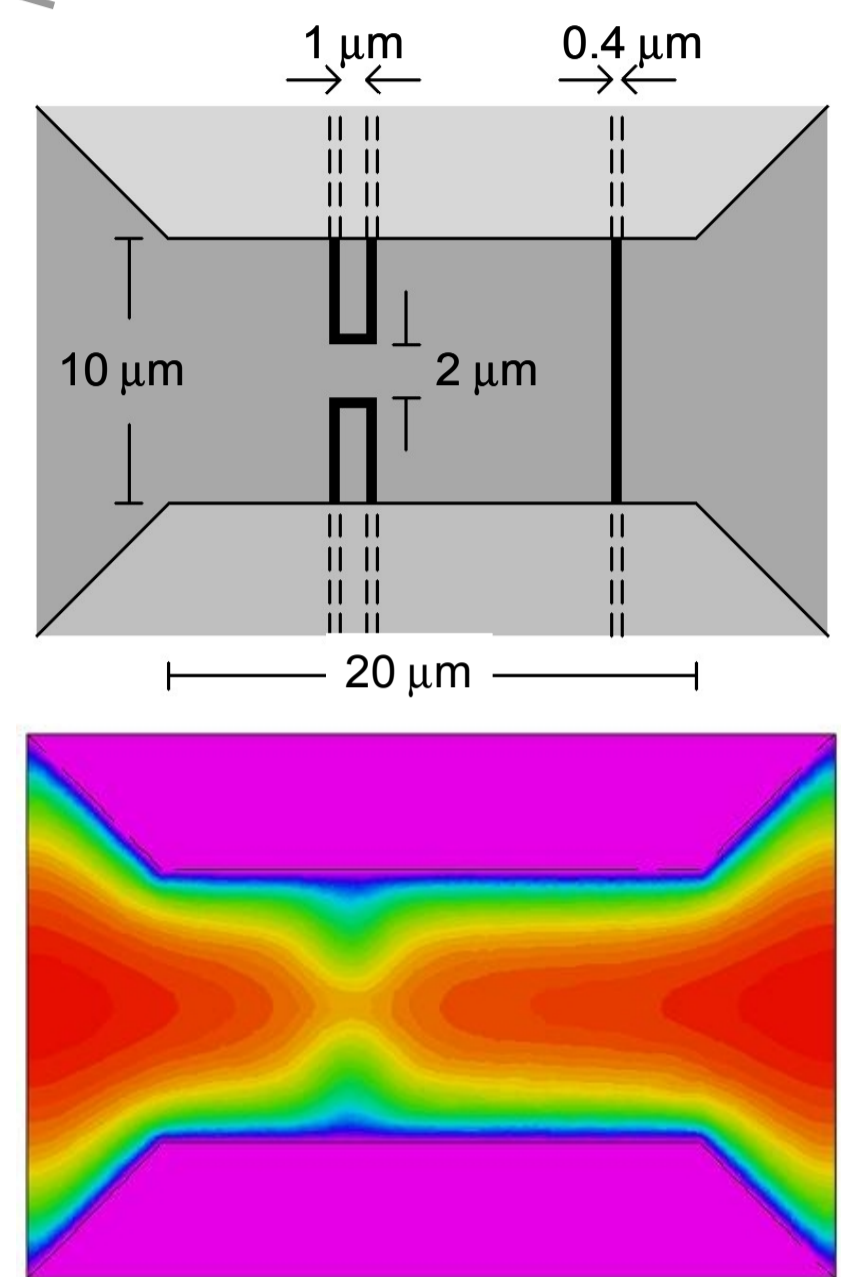
Typical dimensions:  $d = 1.5 \mu\text{m}$ ,  $w = 20 \mu\text{m}$   
 Radius of curvature:  $R = \alpha/\rho gh + n_s^2 e^2 / 2\epsilon\epsilon_0$   
 Change in depth at channel centre:  $\Delta d \sim 0.1 \mu\text{m}$



Our new device: 2 sets of microchannels act as electron reservoirs.

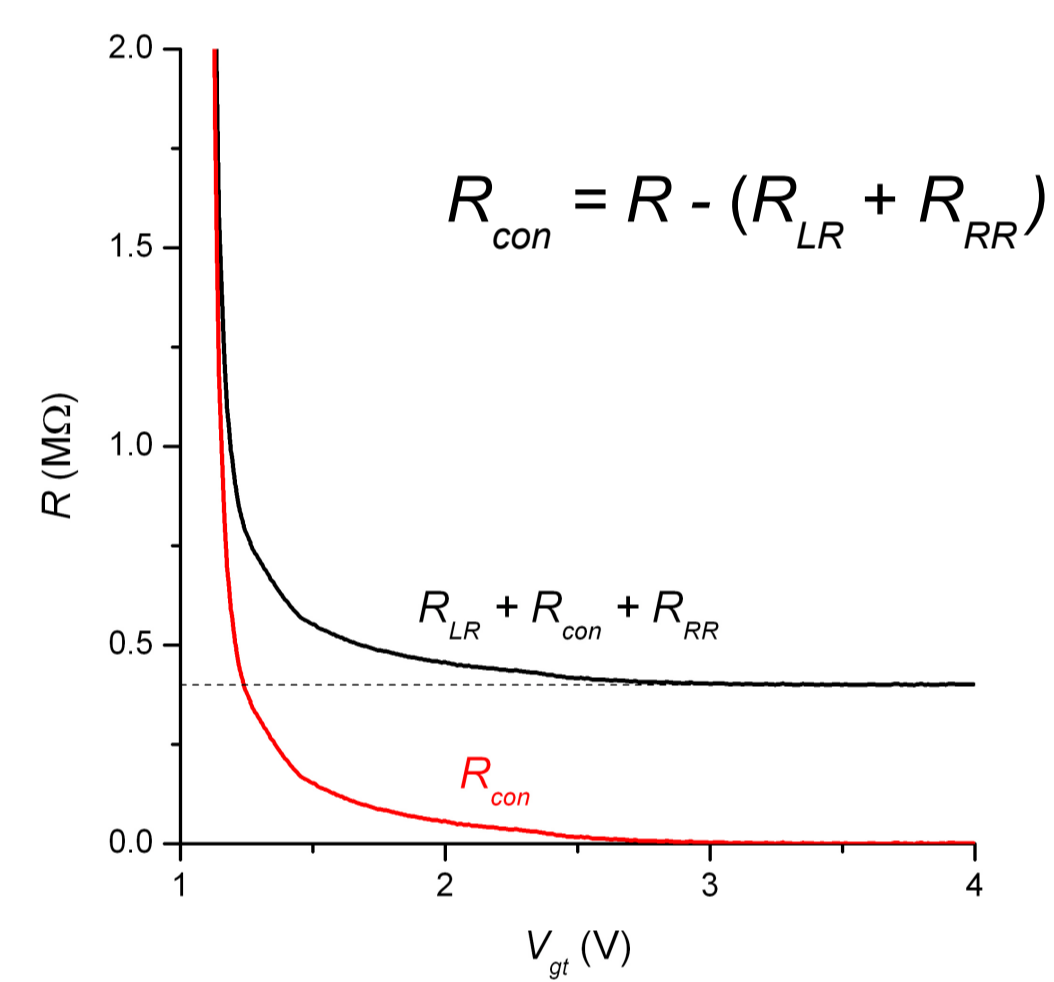
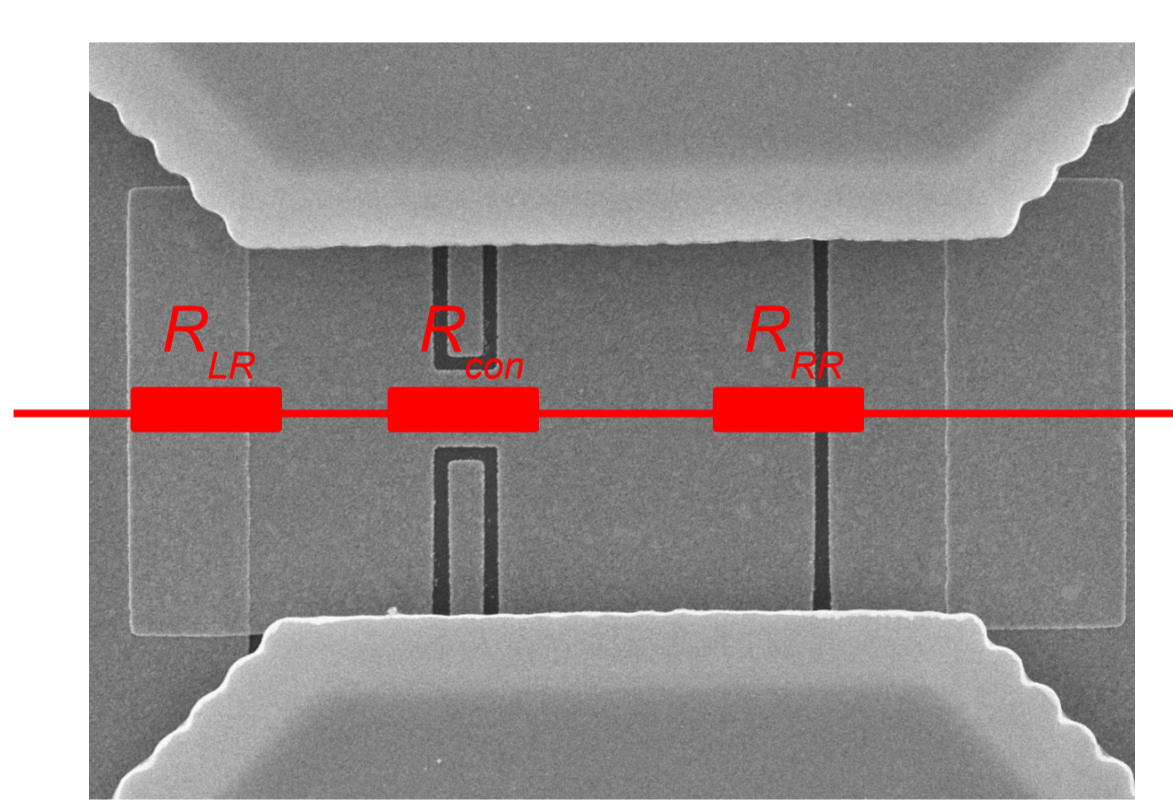
A split-gate is fabricated underneath the helium between the reservoirs.

Finite element modelling shows that a saddle-point potential is formed as the split-gate is swept negative.

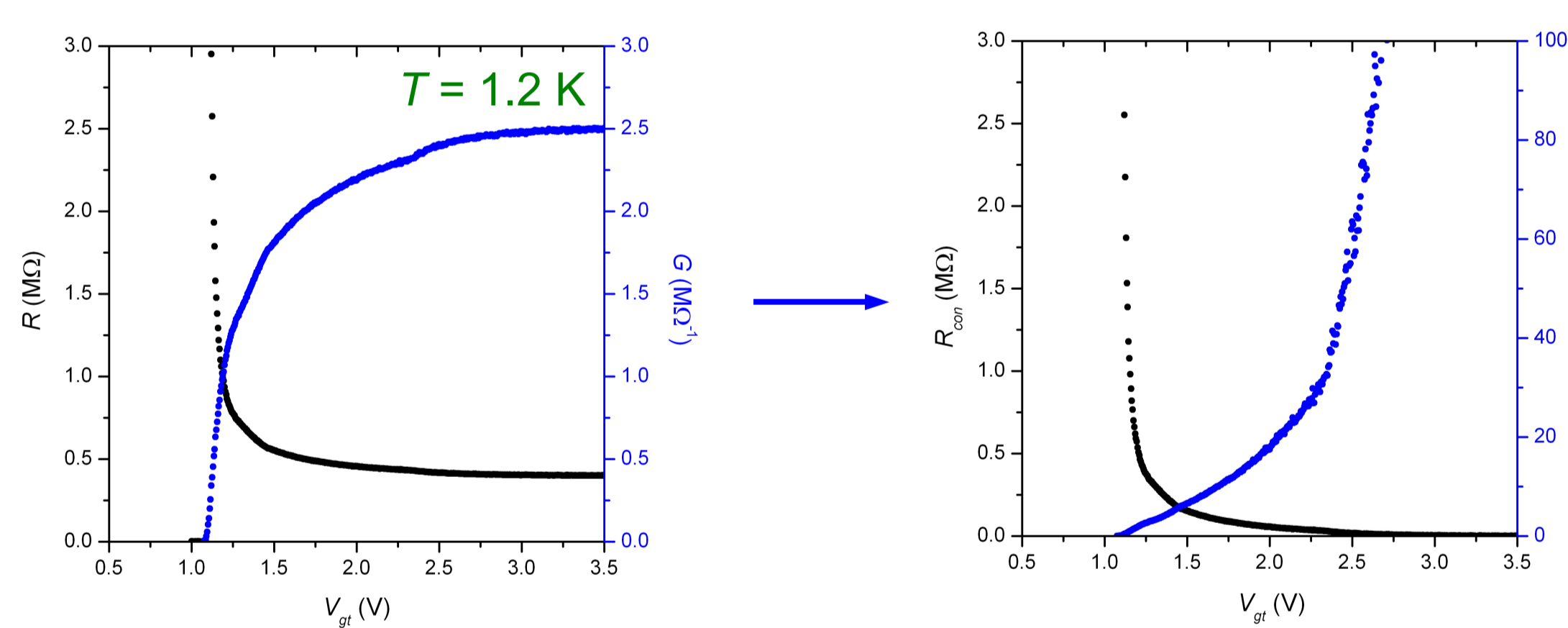


## Constriction Conductance

Assume: The measured resistance  $R$  is the sum of the resistances of the two reservoirs and of the constriction:

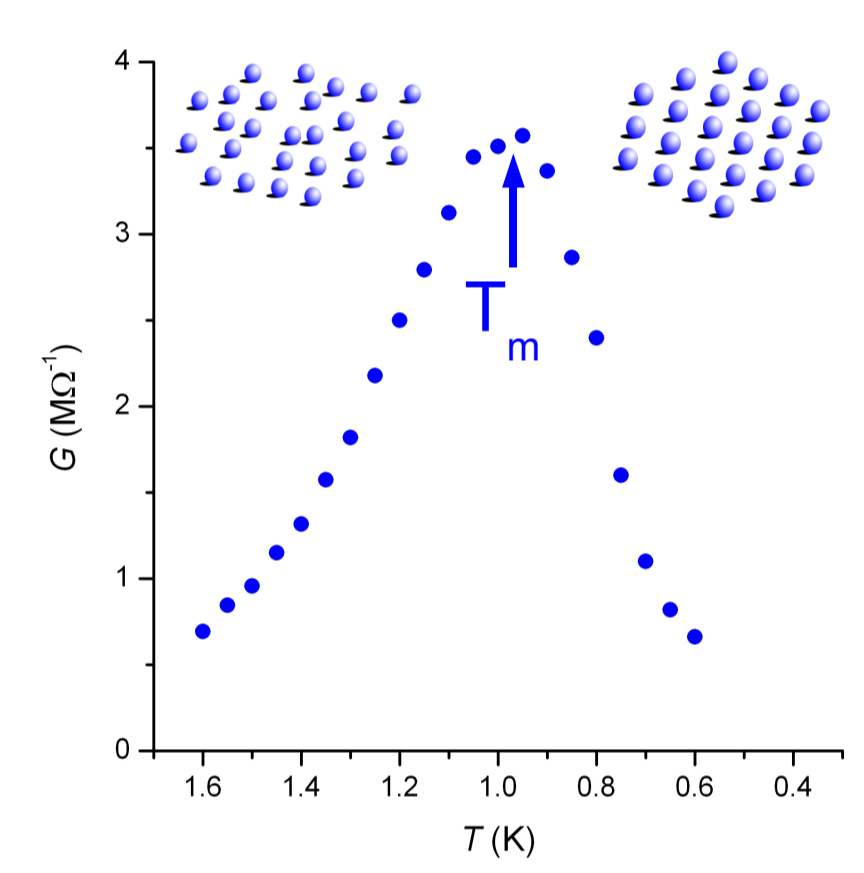
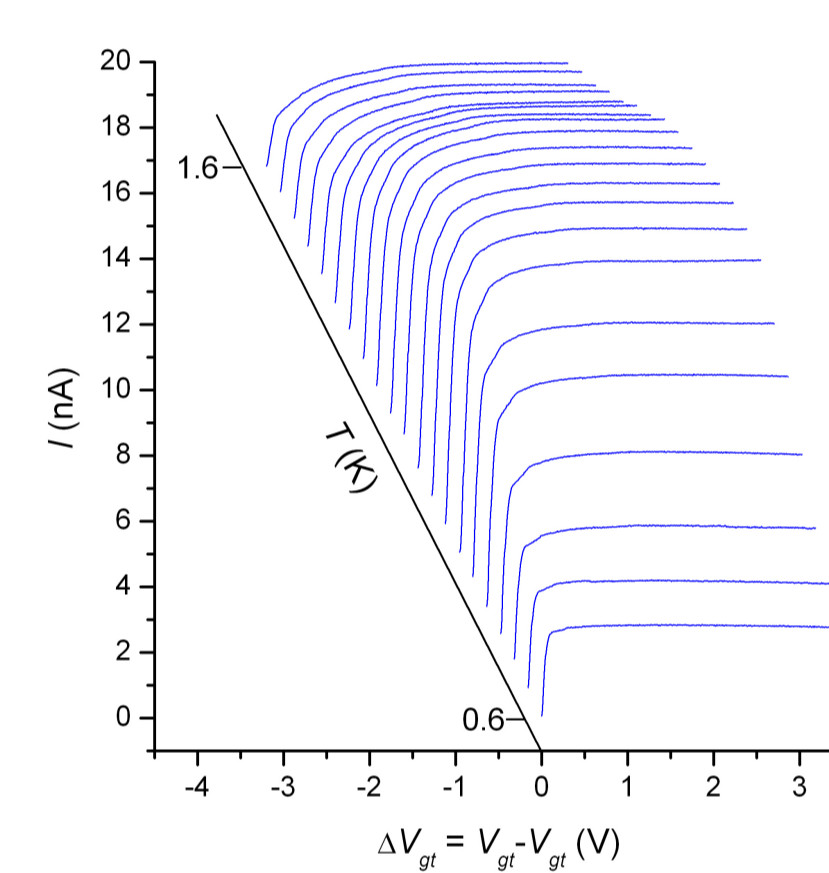


$$G_{con} = 1 / R_{con}$$

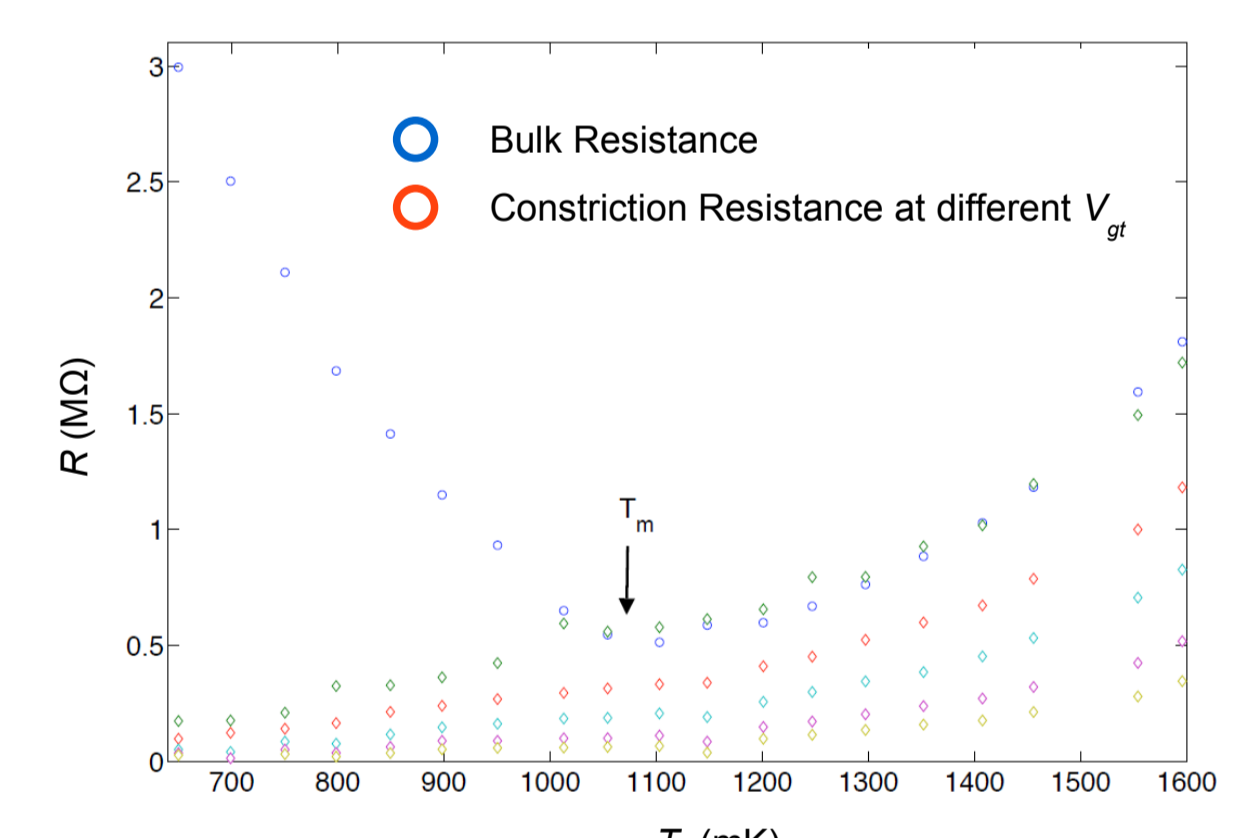
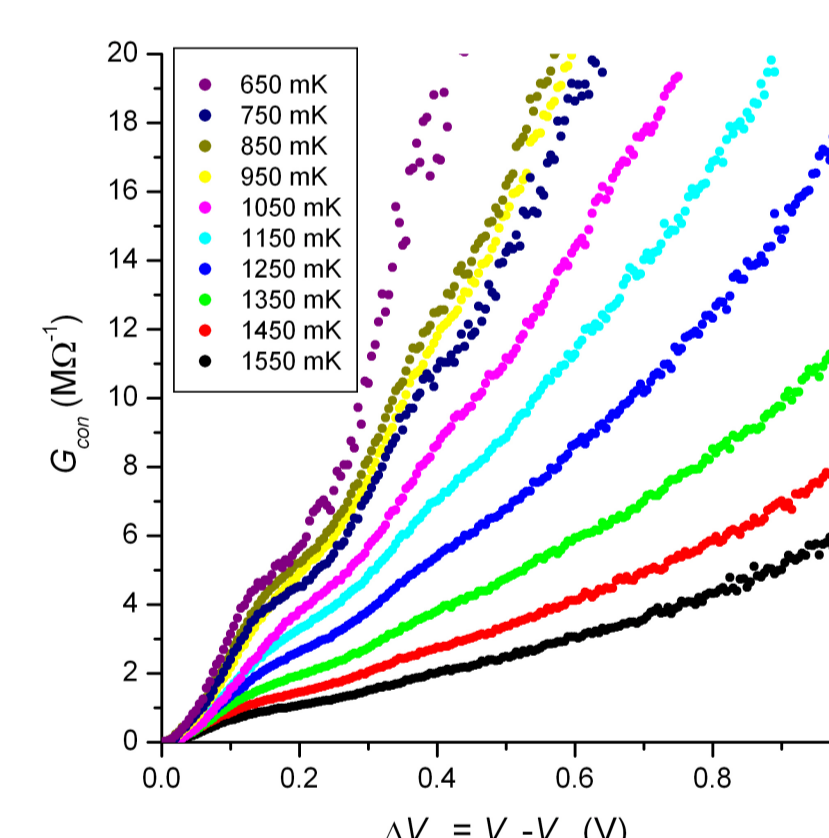


## Temperature Dependence

Measure  $I$  vs  $V_{gr}$  at different  $T$ : See Wigner solid transition occur at  $\sim 1$  K:



The conductance of the constriction continues to increase with decreasing temperature.



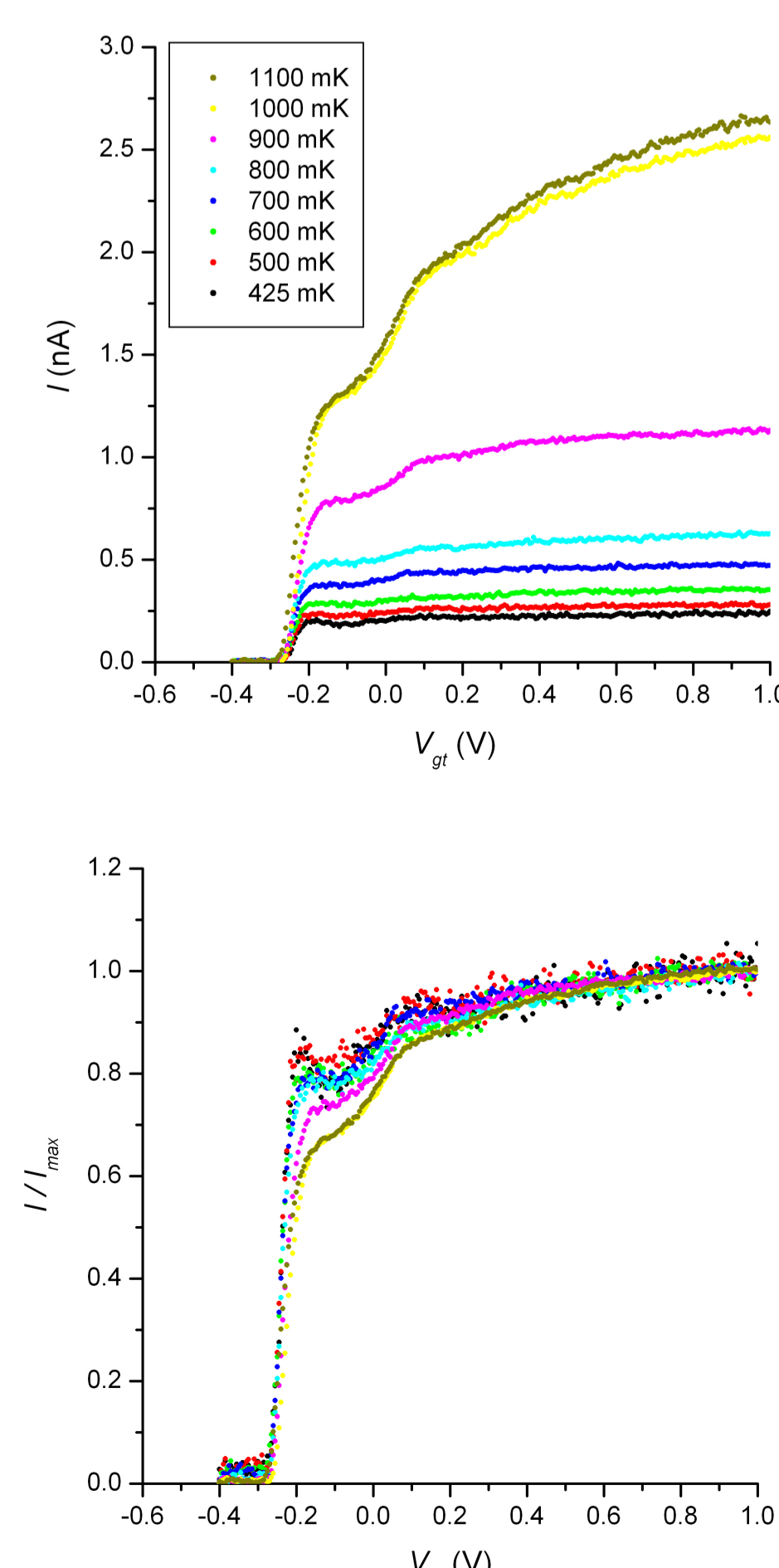
## Development of 'Step' Structure

At low driving voltage, high densities...

We again see the conductance decrease with temperature due to the formation of the Wigner solid.

The 'step'-like structure observed as the gate voltage is swept negative becomes more pronounced and peak-like at low temperatures.

May be related to the melting or sliding of the Wigner solid at the constriction..?



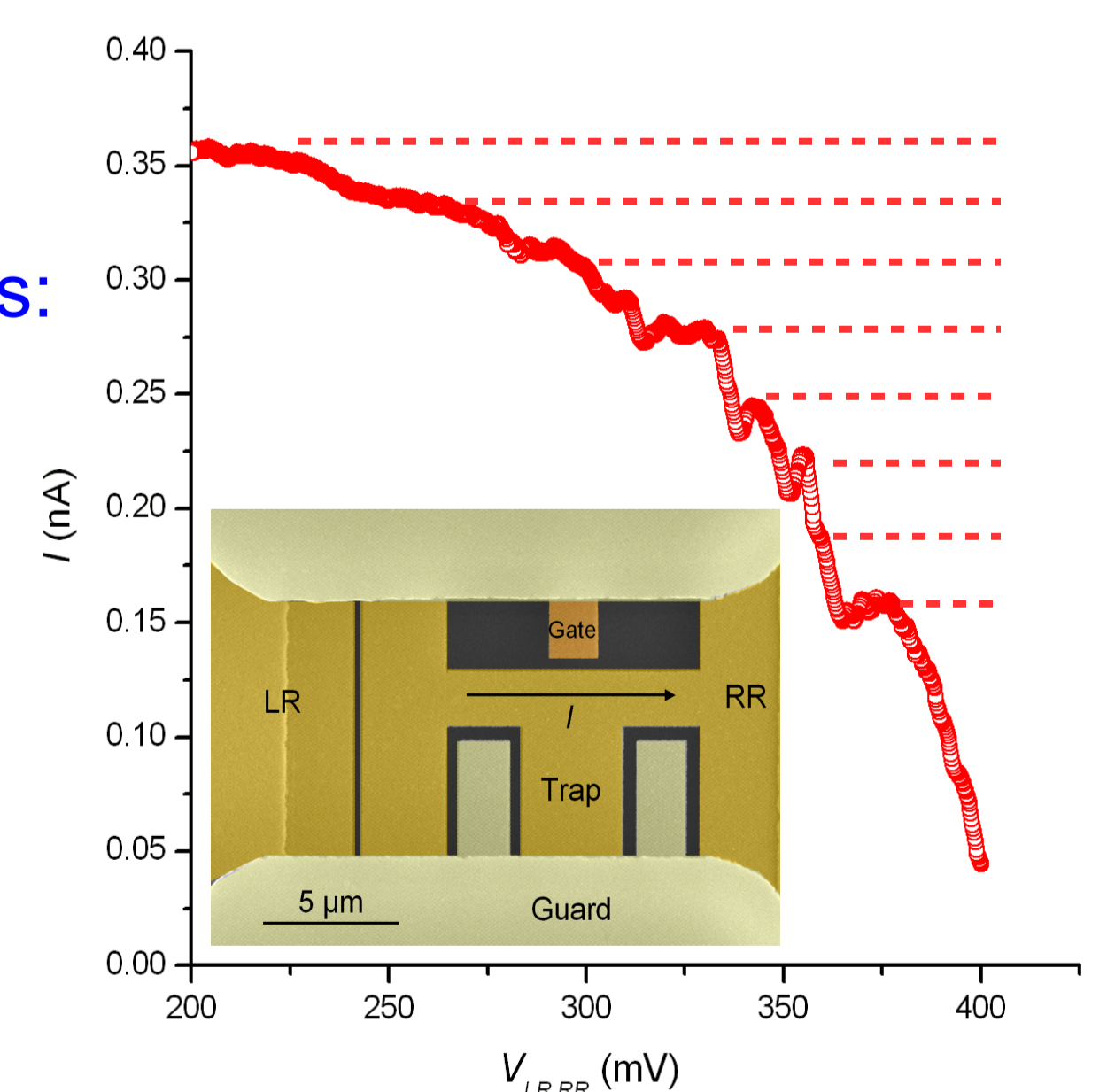
## Future Work

For two potential barriers in series:

$$V_B \sim f(N_e) \quad (N_e \text{ electrons in trap})$$

$$\rightarrow I \sim f(N_e)$$

A single-electron device!



## Summary

- The transport properties of electrons at a point constriction are highly temperature dependent in the liquid and Wigner solid phase.
- We may separate the conductance of the constriction from the total conductance of the electron system.
- We measure no increase in the constriction conductance due to Bragg-Cherenkov scattering of the Wigner solid although at high electron densities there is some evidence for crystal melting/sliding.
- By creating two potential barriers in series it may be possible to create single-electron devices.